

Справочный раздел  
Интернет Портала «Радиодар»

ТЕХНИЧЕСКИЙ СПРАВОЧНИК  
«Мощный БТИЗ (IGBT) транзистор FGH40N60SFD  
производства фирмы ON Semiconductor»

Версия:	1
Ревизия:	3
Дата:	05.02.2020

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**ПЕРЕЙТИ В МАГАЗИН**

# IGBT - Field Stop 600 V, 40 A

## FGH40N60SFDTU, FGH40N60SFDTU-F085

### Description

Using Novel Field Stop IGBT Technology, ON Semiconductor's new series of Field Stop IGBTs offer the optimum performance for Automotive Chargers, Inverter, and other applications where low conduction and switching losses are essential.

### Features

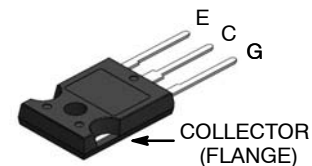
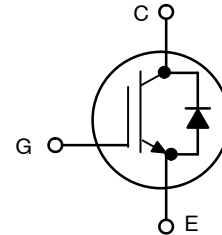
- High Current Capability
- Low Saturation Voltage:  $V_{CE(sat)} = 2.3 \text{ V @ } I_C = 40 \text{ A}$
- High Input Impedance
- Fast Switching
- Qualified to Automotive Requirements of AEC-Q101 (FGH40N60SFDTU-F085)
- These Devices are Pb-Free and are RoHS Compliant

### Applications

- Automotive Chargers, Converters, High Voltage Auxiliaries
- Inverters, PFC, UPS

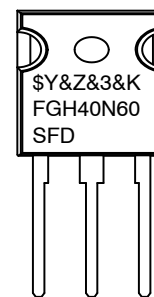


ON Semiconductor®

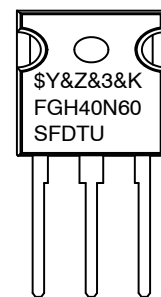


TO-247-3LD  
CASE 340CK

### MARKING DIAGRAM



Industrial



Automotive

\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FGH40N60SFD, FGH40N60SFDTU	= Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FGH40N60SFDTU, FGH40N60SFDTU-F085

## ABSOLUTE MAXIMUM RATINGS

Description		Symbol	Ratings	Unit
Collector to Emitter Voltage		$V_{CES}$	600	V
Gate to Emitter Voltage		$V_{GES}$	$\pm 20$	V
Transient Gate-to-Emitter Voltage			$\pm 30$	V
Collector Current	$T_C = 25^\circ\text{C}$	$I_C$	80	A
	$T_C = 100^\circ\text{C}$		40	A
Pulsed Collector Current	$T_C = 25^\circ\text{C}$	$I_{CM}$ (Note 1)	120	A
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	290	W
	$T_C = 100^\circ\text{C}$		116	W
Operating Junction Temperature		$T_J$	-55 to +150	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	-55 to +150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		$T_L$	300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: Pulse width limited by max. junction temperature.

## THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$ (IGBT)	0.43	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$ (Diode)	1.45	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	$^\circ\text{C}/\text{W}$

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Package Method	Reel Size	Tape Width	Quantity
FGH40N60SFDTU	FGH40N60SFD	TO-247	Tube	-	-	30
FGH40N60SFDTU-F085*	FGH40N60SFDTU	TO-247	Tube	-	-	30

\*Qualified to Automotive Requirements of AEC-Q101

## ELECTRICAL CHARACTERISTICS OF THE IGBT ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector to Emitter Breakdown Voltage	$BV_{CES}$	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	600	-	-	V
Temperature Coefficient of Breakdown Voltage	$\Delta BV_{CES}/\Delta T_J$	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	-	0.6	-	$\text{V}/^\circ\text{C}$
Collector Cut-Off Current	$I_{CES}$	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	$\mu\text{A}$
G-E Leakage Current	$I_{GES}$	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	$\pm 400$	nA

### ON CHARACTERISTICS

G-E Threshold Voltage	$V_{GE(th)}$	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	4.0	4.7	6.5	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	-	2.3	2.9	V
		$I_C = 40\text{ A}, V_{GE} = 15\text{ V}, T_C = 125^\circ\text{C}$	-	2.5	-	V

### DYNAMIC CHARACTERISTICS

Input Capacitance	$C_{ies}$	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	1920	-	pF
Output Capacitance	$C_{oes}$		-	190	-	pF
Reverse Transfer Capacitance	$C_{res}$		-	65	-	pF

## FGH40N60SFDTU, FGH40N60SFDTU-F085

### ELECTRICAL CHARACTERISTICS OF THE IGBT ( $T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 400\text{ V}, I_C = 40\text{ A},$ $R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$	-	21	-	ns
Rise Time	$t_r$		-	35	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	138	-	ns
Fall Time	$t_f$		-	18	54	ns
Turn-On Switching Loss	$E_{on}$		-	1.23	-	mJ
Turn-Off Switching Loss	$E_{off}$		-	0.38	-	mJ
Total Switching Loss	$E_{ts}$		-	1.61	-	mJ
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 400\text{ V}, I_C = 40\text{ A},$ $R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 125^\circ\text{C}$	-	21	-	ns
Rise Time	$t_r$		-	39	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	144	-	ns
Fall Time	$t_f$		-	48	-	ns
Turn-On Switching Loss	$E_{on}$		-	1.58	-	mJ
Turn-Off Switching Loss	$E_{off}$		-	0.58	-	mJ
Total Switching Loss	$E_{ts}$		-	2.16	-	mJ
Total Gate Charge	$Q_g$	$V_{CE} = 400\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	-	121	-	nC
Gate to Emitter Charge	$Q_{ge}$		-	16	-	nC
Gate to Collector Charge	$Q_{gc}$		-	68	-	nC

### ELECTRICAL CHARACTERISTICS OF THE DIODE ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Diode Forward Voltage	$V_{FM}$	$I_F = 20\text{ A}$	$T_C = 25^\circ\text{C}$	-	1.80	2.6	V
			$T_C = 125^\circ\text{C}$	-	1.70	-	
Diode Reverse Recovery Time	$t_{rr}$	$I_F = 20\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	68	-	ns
			$T_C = 125^\circ\text{C}$	-	240	-	
Diode Reverse Recovery Charge	$Q_{rr}$		$T_C = 25^\circ\text{C}$	-	160	-	nC
			$T_C = 125^\circ\text{C}$	-	840	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# FGH40N60SFDTU, FGH40N60SFDTU-F085

## TYPICAL PERFORMANCE CHARACTERISTICS

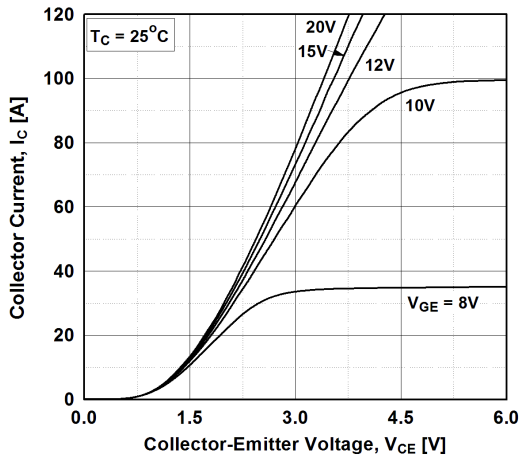


Figure 1. Typical Output Characteristics

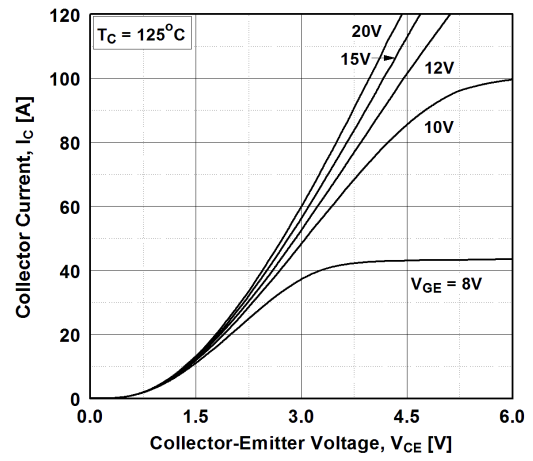


Figure 2. Typical Output Characteristics

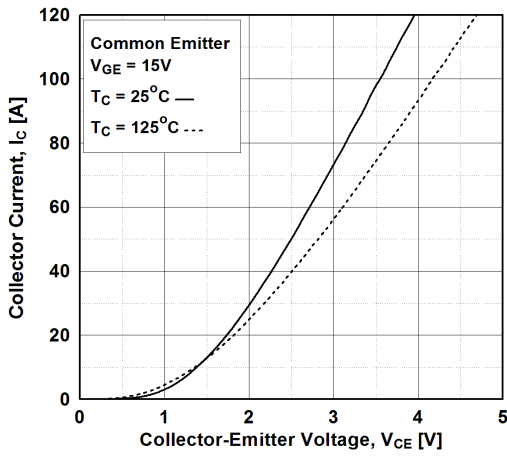


Figure 3. Typical Saturation Voltage Characteristics

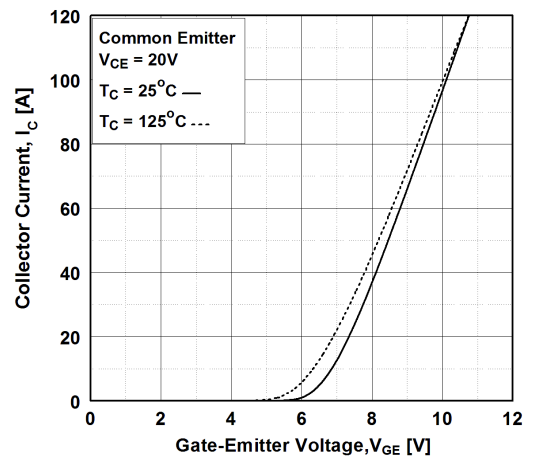


Figure 4. Transfer Characteristics

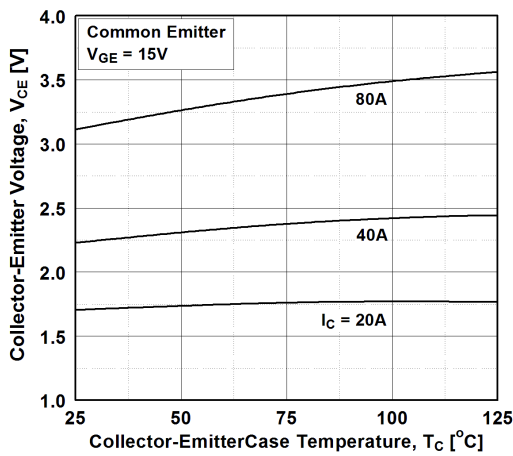


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

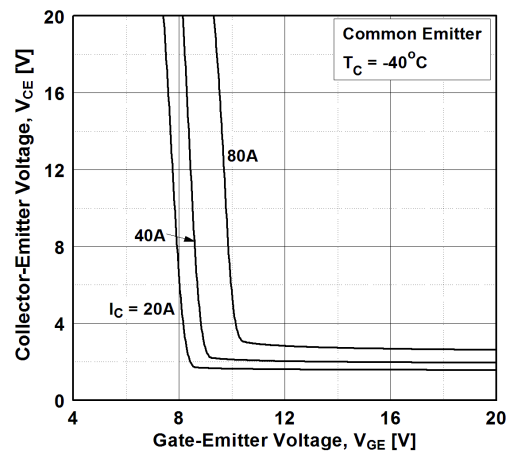


Figure 6. Saturation Voltage vs.  $V_{GE}$

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

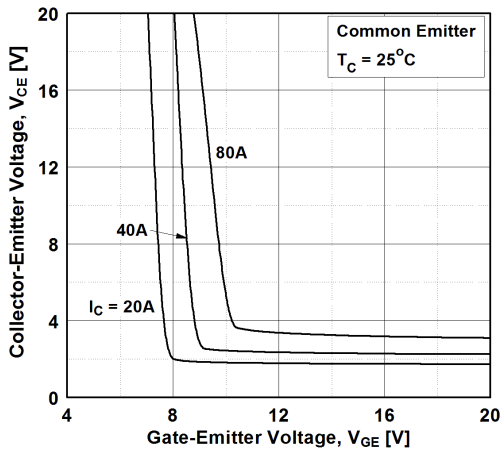


Figure 7. Saturation Voltage vs.  $V_{GE}$

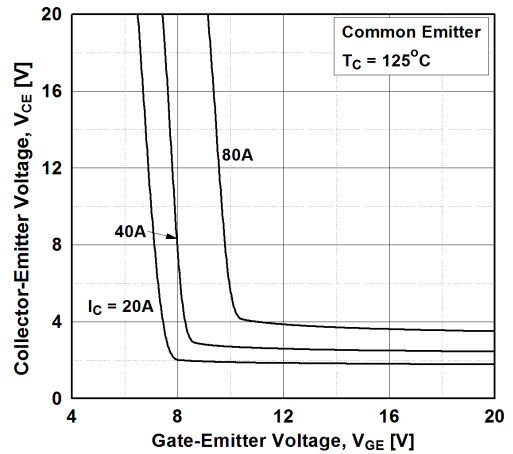


Figure 8. Saturation Voltage vs.  $V_{GE}$

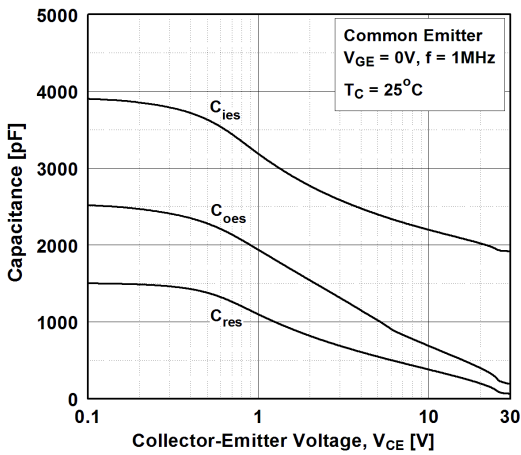


Figure 9. Capacitance Characteristics

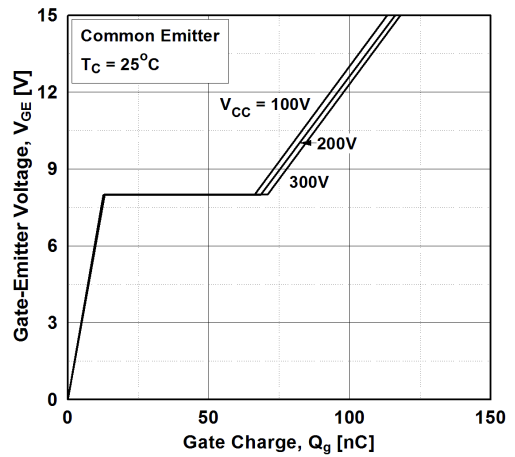


Figure 10. Gate Charge Characteristics

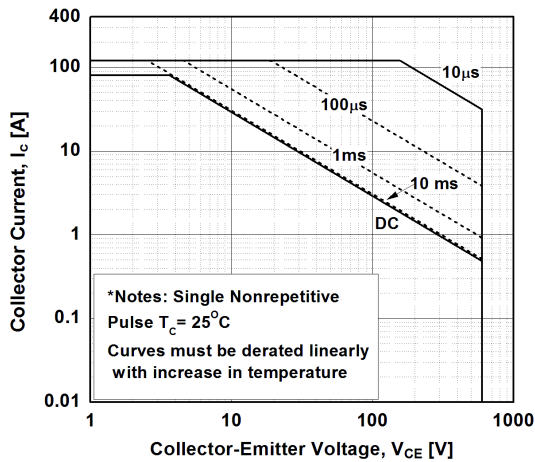


Figure 11. SOA Characteristics

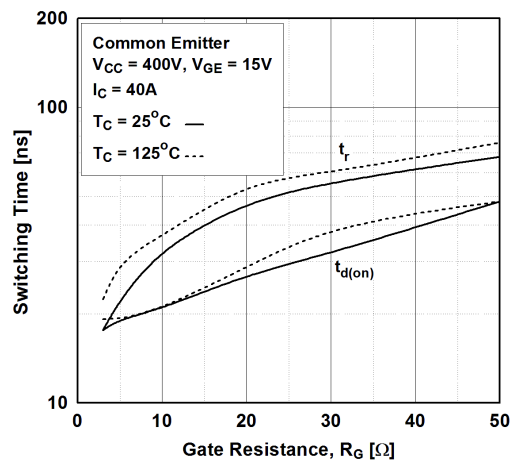


Figure 12. Turn-on Characteristics vs. Gate Resistance

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

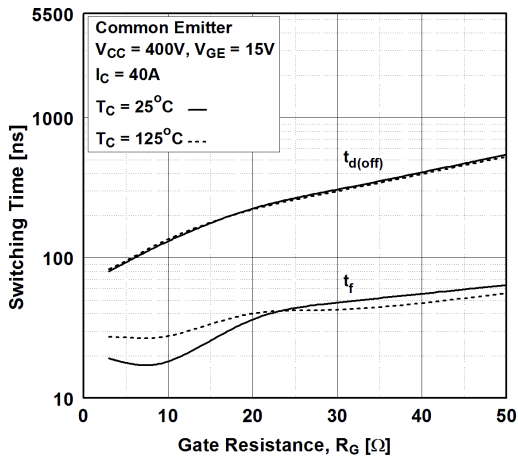


Figure 13. Turn-Off Characteristics vs. Gate Resistance

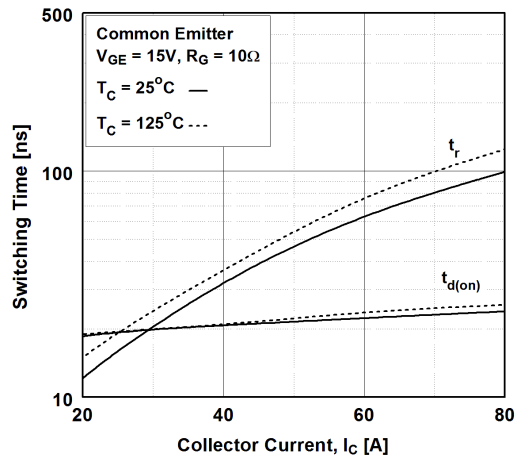


Figure 14. Turn-On Characteristics vs. Collector Current

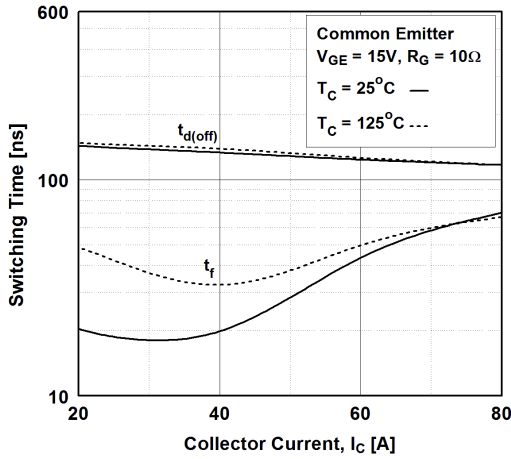


Figure 15. Turn-Off Characteristics vs. Collector Current

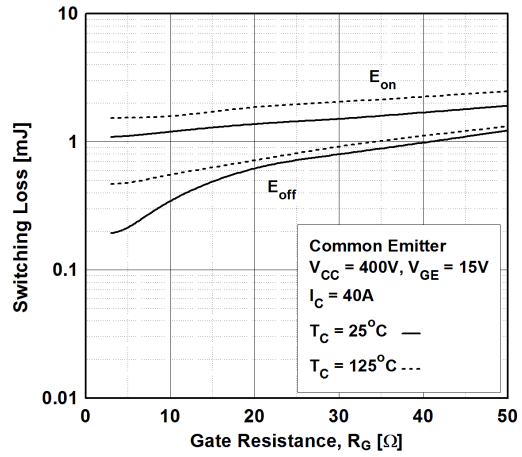


Figure 16. Switching Loss vs. Gate Resistance

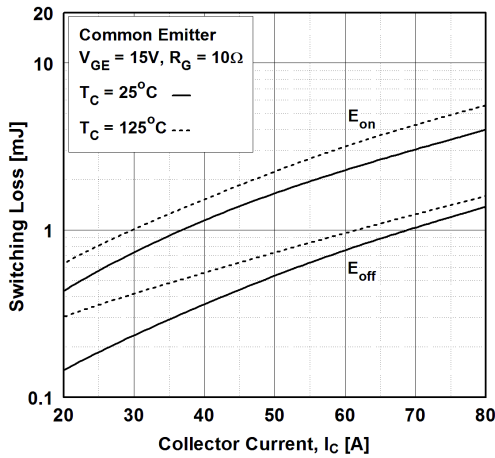


Figure 17. Switching Loss vs. Collector Current

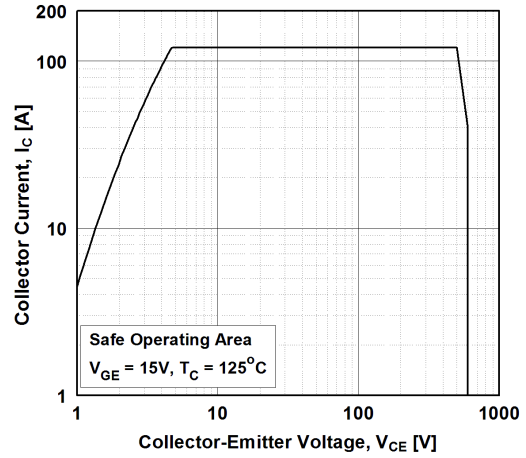


Figure 18. Turn-Off Switching SOA Characteristics

# FGH40N60SFDTU, FGH40N60SFDTU-F085

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

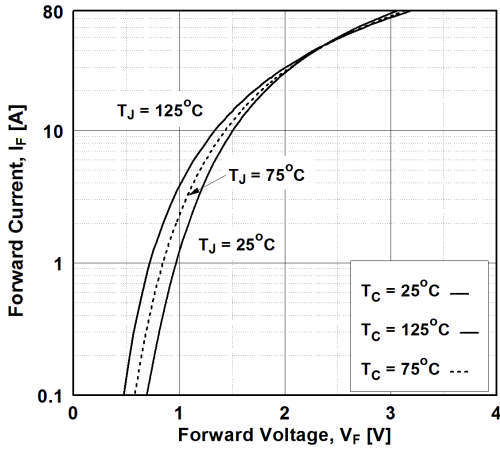


Figure 19. Forward Characteristics

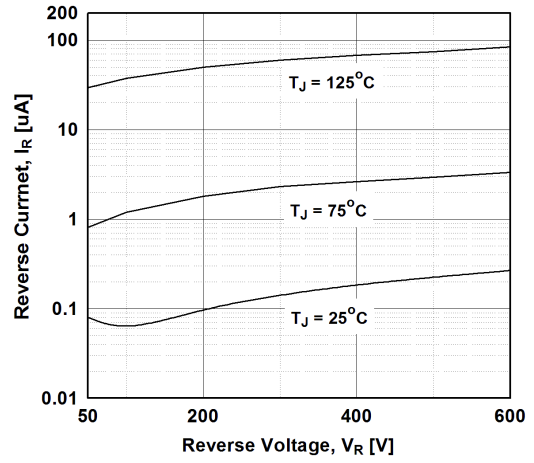


Figure 20. Reverse Current

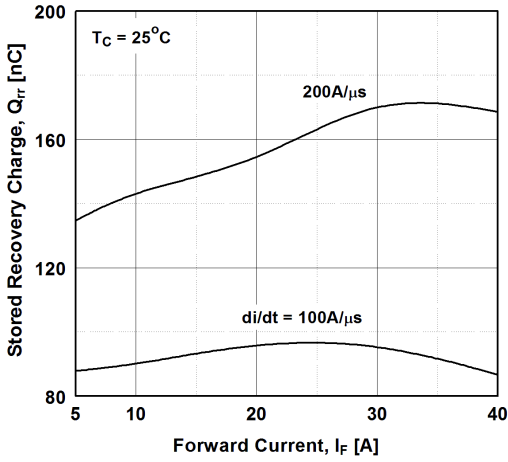


Figure 21. Stored Charge

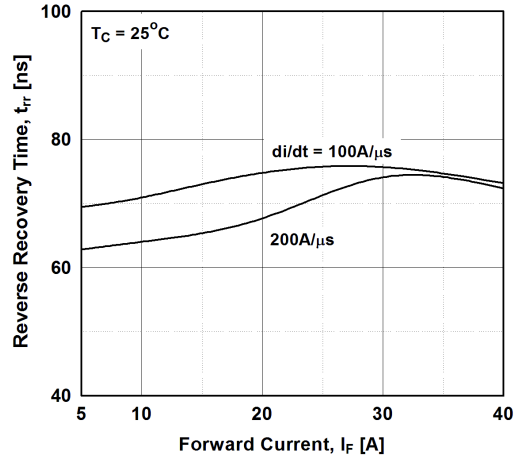


Figure 22. Reverse Recovery Time

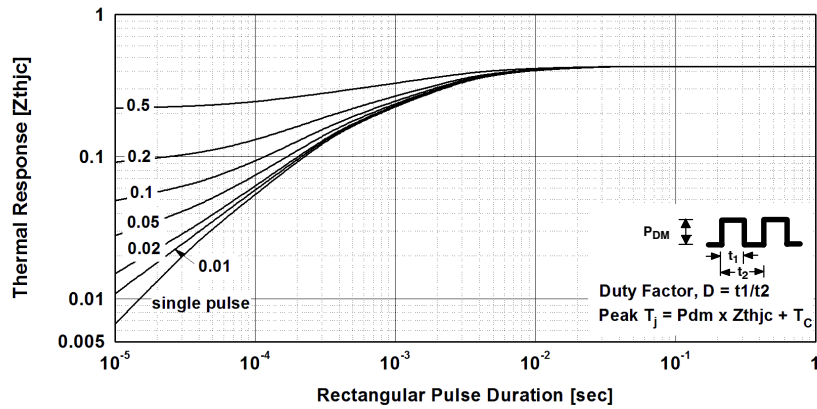


Figure 23. Transient Thermal Impedance of IGBT





**TO-247-3LD SHORT LEAD**  
**CASE 340CK**  
**ISSUE A**

DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

**GENERIC MARKING DIAGRAM\***




- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
$\phi P$	3.51	3.58	3.65
$\phi P1$	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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